

N-channel TrenchMOS FET Rev. 01 — 4 October 2010

Product data sheet

1. **Product profile**

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for standard and logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|--|--|-----|------|-----|------|
| V_{DS} | drain-source voltage | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$ | - | - | 75 | V |
| I _D | drain current | $V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> | - | - | 33 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | - | - | 80 | W |
| Static chara | acteristics | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 12 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{}$ | - | 24.5 | 29 | mΩ |
| Avalanche | ruggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | $I_D = 33$ A; $V_{sup} \le 75$ V; $R_{GS} = 50$ Ω ; $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; unclamped | - | - | 42 | mJ |
| Dynamic ch | naracteristics | | | | | |
| Q_{GD} | gate-drain charge | I_D = 25 A; V_{DS} = 60 V; V_{GS} = 10 V; see <u>Figure 13</u> ; see <u>Figure 14</u> | - | 9.4 | - | nC |



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2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|-----------------------|
| 1 | G | gate | | _ |
| 2 | D | drain | mb | D |
| 3 | S | source | | $G \longrightarrow A$ |
| mb | D | mounting base; connected to drain | 1 3 | mbb076 S |
| | | | SOT428 (DPAK) | |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|---|---------|
| | Name | Description | Version |
| BUK6226-75C | DPAK | plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) | SOT428 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|--|------------|-----|-----|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | 75 | V |
| V _{GS} | gate-source voltage | DC | <u>[1]</u> | -16 | 16 | V |
| | | Pulsed | [2] | -20 | 20 | V |
| I _D | drain current | $T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$ | | - | 33 | Α |
| | | $T_{mb} = 100 ^{\circ}\text{C}; V_{GS} = 10 ^{\circ}\text{V}; \text{see} \frac{\text{Figure 1}}{}$ | | - | 23 | Α |
| I _{DM} | peak drain current | T_{mb} = 25 °C; $t_p \le 10 \mu s$; pulsed; see Figure 3 | | - | 130 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | | - | 80 | W |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| Tj | junction temperature | | | -55 | 175 | °C |
| Source-drain | diode | | | | | |
| Is | source current | $T_{mb} = 25 ^{\circ}C$ | | - | 33 | Α |
| I _{SM} | peak source current | $t_p \le 10 \mu\text{s}; \text{ pulsed}; T_{mb} = 25 ^{\circ}\text{C}$ | | - | 130 | Α |
| Avalanche rug | ggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I_D = 33 A; $V_{sup} \le$ 75 V; R_{GS} = 50 Ω ; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped | | - | 42 | mJ |
| E _{DS(AL)R} | repetitive drain-source avalanche energy | | [3][4][5] | - | - | J |

^{[1] -16}V accumulated duration not to exceed 168 hrs.

^[2] Accumulated pulse duration not to exceed 5 mins.

^[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

^[4] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

^[5] Refer to application note AN10273 for further information.

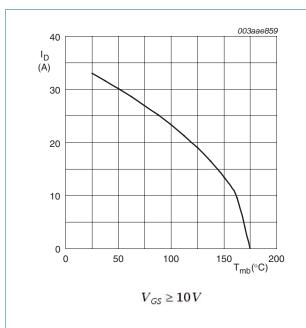


Fig 1. Continuous drain current as a function of mounting base temperature

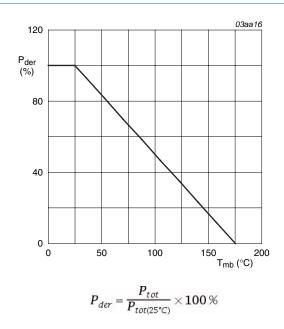
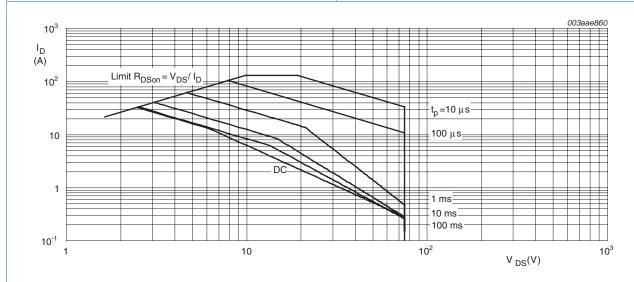


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 T_{mb} = 25 °C; I_{DM} is a single pulse

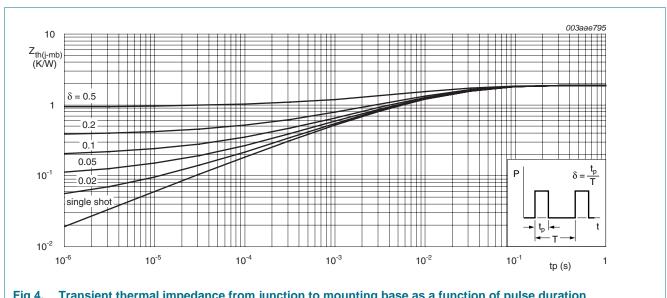
Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

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Thermal characteristics

Table 5. **Thermal characteristics**

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------|---|--------------|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see Figure 4 | - | - | 1.87 | K/W |



Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|----------------------------------|---|----------|--------|------|------|
| Static char | acteristics | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | 75 | - | - | V |
| | | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$ | 68 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 9</u> ; see <u>Figure 10</u> | 1.8 | 2.3 | 2.8 | V |
| | | $I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 9 | - | - | 3.3 | V |
| | | $I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 9 | 0.8 | - | - | V |
| I _{DSS} | drain leakage current | $V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$ | - | - | 500 | μΑ |
| | | $V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 0.02 | 1 | μΑ |
| I _{GSS} | gate leakage current | $V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ °C}$ | - | 2 | 100 | nΑ |
| | | $V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$ | - | 2 | 100 | nΑ |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 12 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> | - | 24.5 | 29 | mΩ |
| | | $V_{GS} = 4.5 \text{ V}; I_D = 12 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11 | - | - 30 4 | 40 | mΩ |
| | | $V_{GS} = 5 \text{ V; } I_D = 12 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 11 | - | 28 | 35 | mΩ |
| | | V_{GS} = 10 V; I_D = 12 A; T_j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 11</u> | - | - | 75.4 | mΩ |
| Dynamic c | haracteristics | | | | | |
| | total gate charge | $I_D = 25 \text{ A}$; $V_{DS} = 60 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 13; see Figure 14 | - | 34 | - | nC |
| | | $I_D = 25 \text{ A}$; $V_{DS} = 60 \text{ V}$; $V_{GS} = 5 \text{ V}$; see Figure 13; see Figure 14 | - 18.6 - | nC | | |
| Q _{GS} | gate-source charge | $I_D = 25 \text{ A}; V_{DS} = 60 \text{ V}; V_{GS} = 10 \text{ V};$ | - | 5.6 | - | nC |
| Q_GD | gate-drain charge | see Figure 13; see Figure 14 | - | 9.4 | - | nC |
| C _{iss} | input capacitance | $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ | - | 1500 | 2000 | pF |
| C _{oss} | output capacitance | T _j = 25 °C; see <u>Figure 15</u> | - | 128 | 155 | pF |
| C _{rss} | reverse transfer capacitance | | - | 89 | 110 | рF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 55 \text{ V}; R_L = 2.2 \Omega; V_{GS} = 10 \text{ V};$ | - | 11.8 | - | ns |
| t _r | rise time | $R_{G(ext)} = 10 \Omega$ | - | 15.6 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 59 | - | ns |
| t _f | fall time | | - | 31 | - | ns |
| L _D | internal drain inductance | from upper edge of drain mounting base to centre of die ; $T_j = 25 ^{\circ}\text{C}$ | - | 3.5 | - | nΗ |
| L _S | internal source inductance | from source lead to source bond pad ; $T_j = 25 ^{\circ}\text{C}$ | - | 7.5 | - | nΗ |

Table 6. Characteristics ...continued

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|-----------------------|---|-----|-----|-----|------|
| Source-dra | in diode | | | | | |
| V_{SD} | source-drain voltage | $I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 16 | - | 0.8 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_S = 20 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; | - | 42 | - | ns |
| Q _r | recovered charge | $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}$ | - | 74 | - | nC |

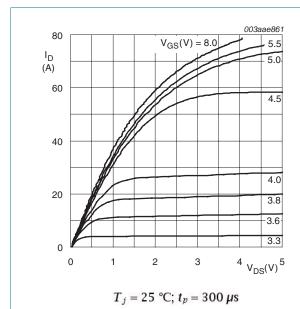


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

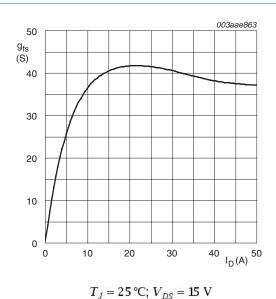


Fig 6. Forward transconductance as a function of drain current; typical values

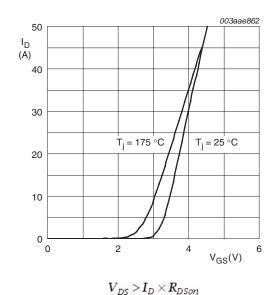
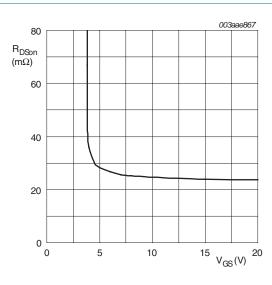


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25$ °C; $I_D = 12$ A

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

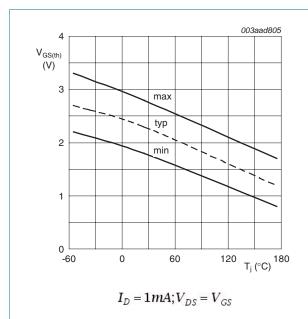
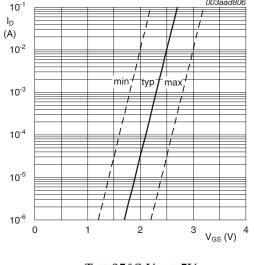


Fig 9. Gate-source threshold voltage as a function of junction temperature



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

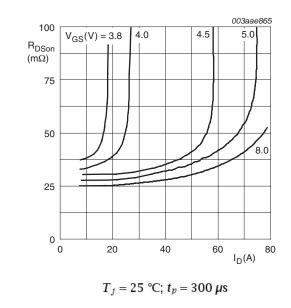


Fig 11. Drain-source on-state resistance as a function of drain current; typical values

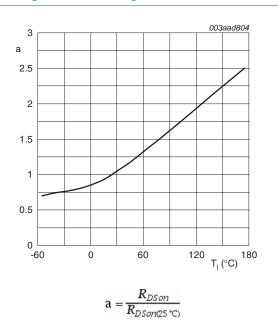
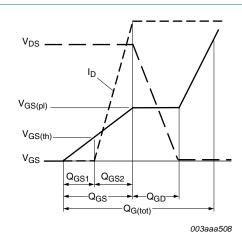


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

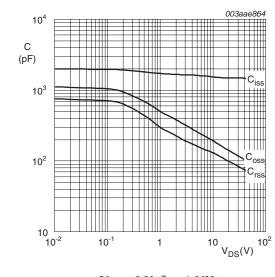


10 003aae866 (V) 7.5 14V V_{DS}= 60V 2.5 Q_G(nC) 40

 $T_j = 25$ °C; $I_D = 25$ A

Fig 13. Gate charge waveform definitions

Fig 14. Gate-source voltage as a function of gate charge; typical values



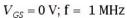


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

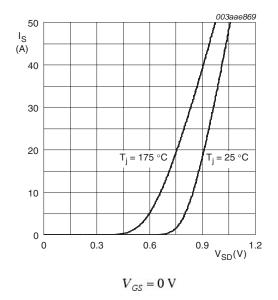


Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

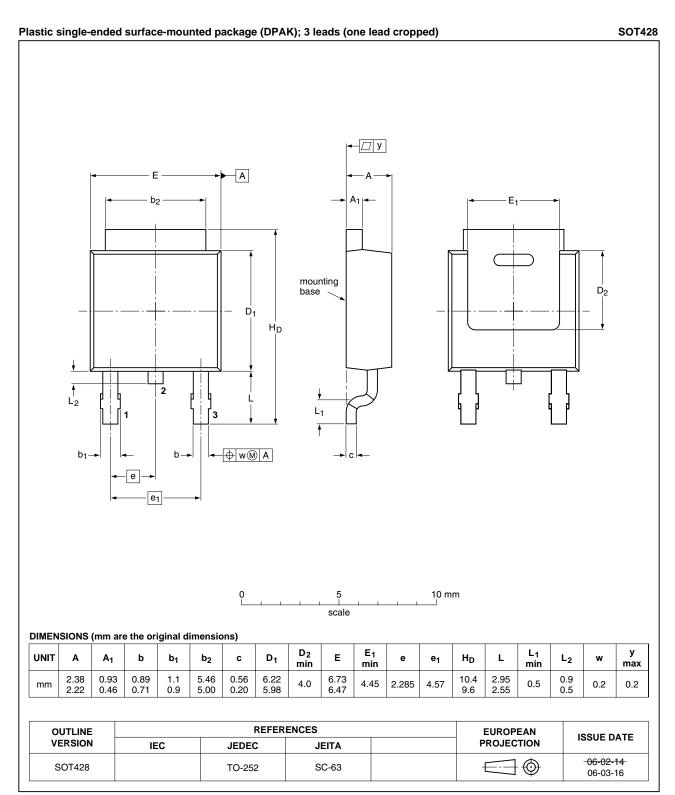


Fig 17. Package outline SOT428 (DPAK)

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8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-----------------|--------------|--------------------|---------------|------------|
| BUK6226-75C v.1 | 20101004 | Product data sheet | - | - |

9. Legal information

9.1 Data sheet status

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|---|---------------|---|
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